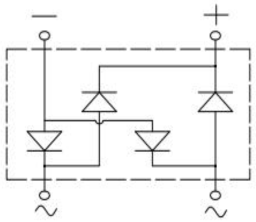
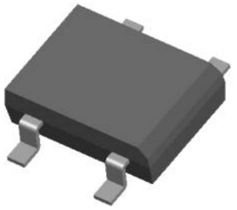
Bridge Rectifier Diode 整流桥





■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Peak Soak Temperature 260℃ 峰值浸润温度 260 度
Package 封装: DB-S

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	DB201S	DB202S	DB203S	DB204S	DB205S	DB206S	DB207S	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	2							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	60							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	40							℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	150℃,-55to+150℃							

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.1		V	I_F=1.5A
Reverse Current (T_A=25℃) 反向电流(T_A=125℃)	I_R			5 500	uA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		19		pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

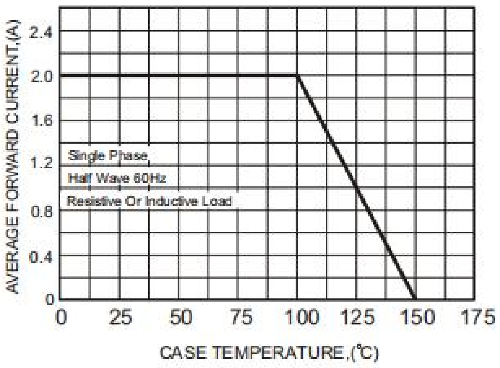


Figure 1: Forward Current Derating Curve

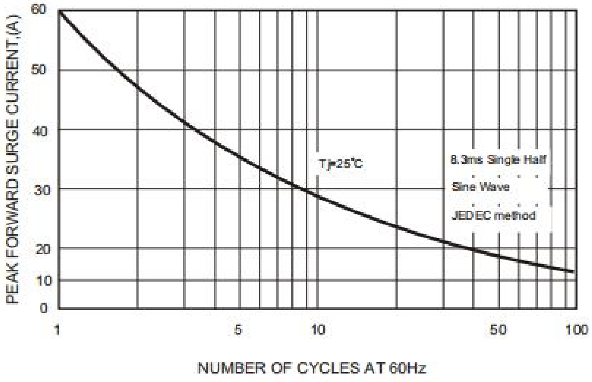


Figure 2: Peak Forward Surge Current

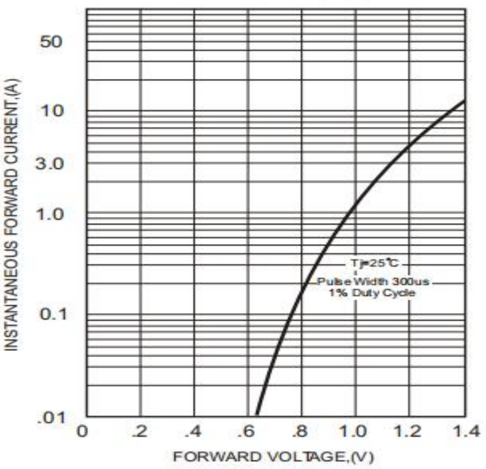


Figure 3:Instantaneous Forward Characteristics

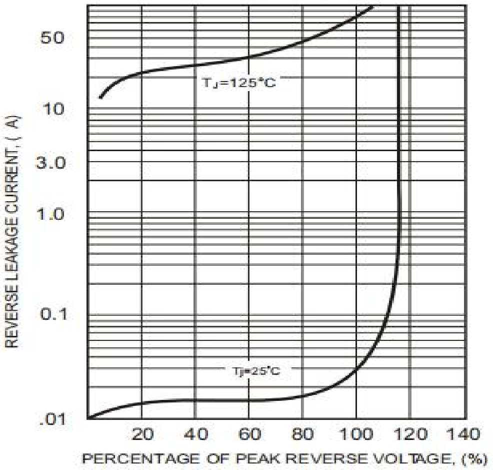
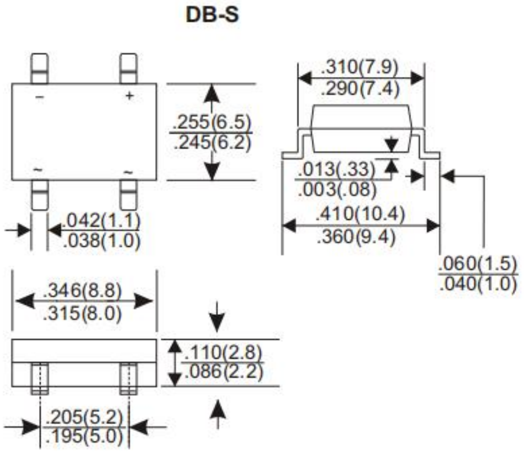


Figure 4: Reverse Leakage Characteristics

■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)